

FORM PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Atty. Docket No. FIS920030183US1	Application No. 10/605,108
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)		Applicant Dureseti CHIDAMBARRAO, et al.			
		Filing Date 09/09/2003		Group 2814	

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Long Pham	6/15/06

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